



CSD88539ND, Dual 60 V N-Channel NexFET™ Power MOSFETs

Features 1

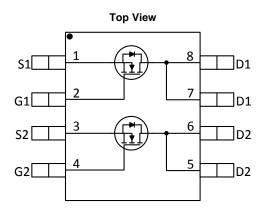
- Ultra-Low Q_a and Q_{ad}
- Avalanche Rated
- Pb Free
- **RoHS** Compliant
- Halogen Free

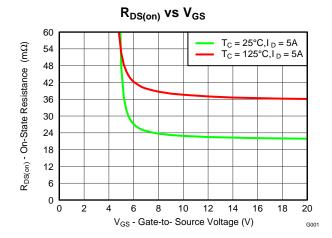
Applications 2

- Half Bridge for Motor Control
- Synchronous Buck Converter

Description 3

This dual SO-8, 60 V, 23 mΩ NexFET™ power MOSFET is designed to serve as a half bridge in lowcurrent motor control applications.





Product Summary

| T _A = 25° | С | TYPICAL VA | UNIT | |
|----------------------|-------------------------------|-----------------|------|----|
| V _{DS} | Drain-to-Source Voltage | 60 | | V |
| Qg | Gate Charge Total (10 V) | 7.2 | nC | |
| Q _{gd} | Gate Charge Gate to Drain 1.1 | | | |
| Б | Drain-to-Source On Resistance | $V_{GS} = 6 V$ | mΩ | |
| R _{DS(on)} | Drain-to-Source On Resistance | $V_{GS} = 10 V$ | 23 | mΩ |
| V _{GS(th)} | Threshold Voltage | 3.0 | | V |

Ordering Information

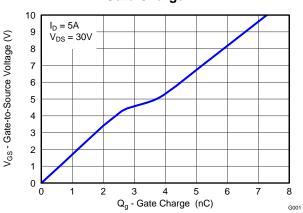
Media Package Device Qty Ship CSD88539ND 2500 13-Inch Reel SO-8 Plastic Tape and Reel Package CSD88539NDT 250 7-Inch Reel

Absolute Maximum Ratings

| T _A = 2 | 5°C | VALUE | UNIT |
|--------------------------------------|----------------------------------------------------------------------------------|------------|------|
| V_{DS} | Drain-to-Source Voltage | 60 | V |
| V_{GS} | Gate-to-Source Voltage | ±20 | V |
| | Continuous Drain Current (Package limited) | 15 | |
| I _D | Continuous Drain Current (Silicon limited), $T_C = 25^{\circ}C$ | 11.7 | А |
| | Continuous Drain Current ⁽¹⁾ | 6.3 | |
| I _{DM} | Pulsed Drain Current (2) | 46 | А |
| PD | Power Dissipation ⁽¹⁾ | 2.1 | W |
| T _J , T _{STG} | Operating Junction and Storage Temperature Range | -55 to 150 | °C |
| E _{AS} | Avalanche Energy, single pulse I_{D} = 22 A, L = 0.1 mH, R_{G} = 25 Ω | 24 | mJ |

(1) Typical $R_{\theta JA} = 60^{\circ}$ C/W on a 1-inch², 2-oz. Cu pad on a 0.06inch thick FR4 PCB

(2) Pulse duration \leq 300 µs, duty cycle \leq 2%



Gate Charge





4 Specifications

Electrical Characteristics 4.1

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------|----------------------------------|---------------------------------------------------------------------------------------------|-----|-----|------|------|
| Static Cl | naracteristics | | · | | | |
| BV _{DSS} | Drain-to-Source Voltage | V _{GS} = 0 V, I _D = 250 µA | 60 | | | V |
| I _{DSS} | Drain-to-Source Leakage Current | V _{GS} = 0 V, V _{DS} = 48 V | | | 1 | μA |
| I _{GSS} | Gate-to-Source Leakage Current | $V_{DS} = 0 V, V_{GS} = 20 V$ | | | 100 | nA |
| V _{GS(th)} | Gate-to-Source Threshold Voltage | $V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$ | 2.6 | 3.0 | 3.6 | V |
| D | Drain to Course On Desistance | V _{GS} = 6 V, I _D = 5 A | | 27 | 34 | mΩ |
| R _{DS(on)} | Drain-to-Source On Resistance | V _{GS} = 10 V, I _D = 5 A | | 23 | 28 | mΩ |
| 9 _{fs} | Transconductance | V _{DS} = 30 V, I _D = 5 A | | 19 | | S |
| Dynamic | Characteristics | · · | | | | |
| C _{iss} | Input Capacitance | | | 570 | 741 | pF |
| C _{oss} | Output Capacitance | V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz | | 70 | 91 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 2.0 | 2.6 | pF |
| R _G | Series Gate Resistance | | | 6.6 | 13.2 | Ω |
| Qg | Gate Charge Total (10 V) | | | 7.2 | 9.4 | nC |
| Q _{gd} | Gate Charge Gate to Drain | | | 1.1 | | nC |
| Q _{gs} | Gate Charge Gate to Source | V _{DS} = 30 V, I _D = 5 A | | 2.7 | | nC |
| Q _{g(th)} | Gate Charge at V _{th} | | | 1.8 | | nC |
| Q _{oss} | Output Charge | V _{DS} = 30 V, V _{GS} = 0 V | | 9.6 | | nC |
| t _{d(on)} | Turn On Delay Time | | | 5 | | ns |
| t _r | Rise Time | | | 9 | | ns |
| t _{d(off)} | Turn Off Delay Time | V _{DS} = 30 V, V _{GS} = 10 V, I _{DS} = 5 A, R _G = 0 Ω | | 14 | | ns |
| t _f | Fall Time | | | 4 | | ns |
| Diode Cl | haracteristics | | · · | | | |
| V_{SD} | Diode Forward Voltage | I _{SD} = 5 A, V _{GS} = 0 V | | 0.8 | 1 | V |
| Q _{rr} | Reverse Recovery Charge | | | 37 | | nC |
| t _{rr} | Reverse Recovery Time | V_{DS} = 30 V, I _F = 5A, di/dt = 300A/µs | | 21 | | ns |

4.2 Thermal Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

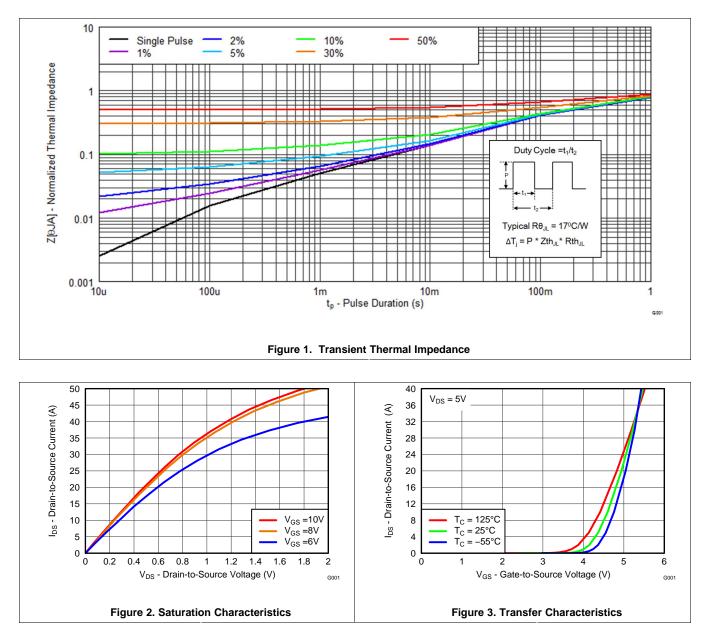
| PARAMETER | MIN | TYP | MAX | UNIT |
|---------------------------------------------------------------------------|-----|-----|-----|------|
| R _{0JL} Junction-to-Lead Thermal Resistance ⁽¹⁾ | | | 20 | °C/W |
| R _{8JA} Junction-to-Ambient Thermal Resistance ⁽¹⁾⁽²⁾ | | | 75 | °C/W |

(1) R_{θJC} is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.
(2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.



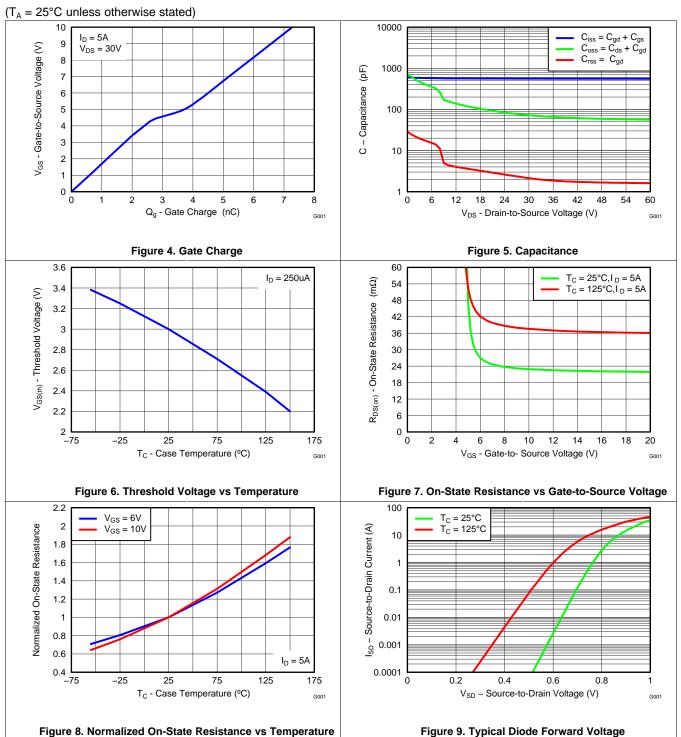
4.3 Typical MOSFET Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



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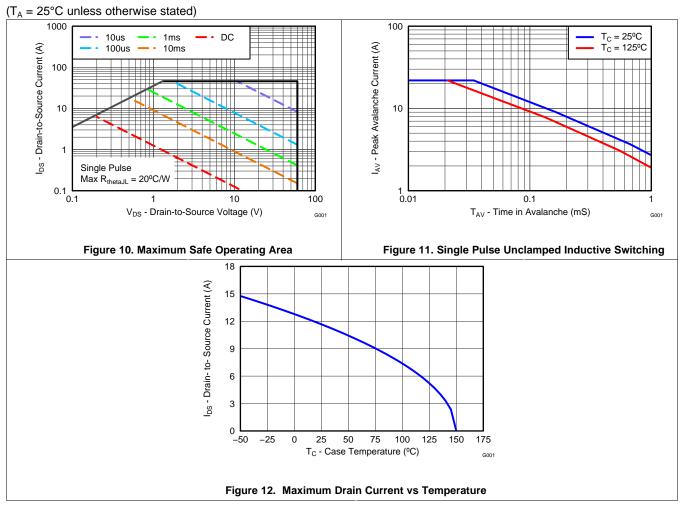
Typical MOSFET Characteristics (continued)



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Typical MOSFET Characteristics (continued)

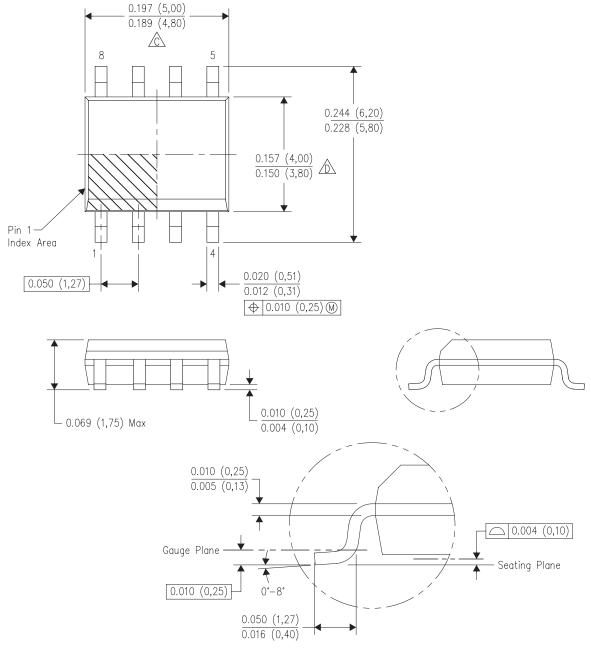


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5 Mechanical Data

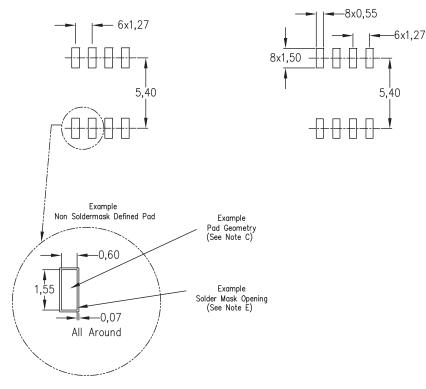
5.1 SO-8 Package Dimensions



- 1. All linear dimensions are in inches (millimeters).
- 2. This drawing is subject to change without notice.
- 3. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- 4. Body width does not include interlead flash. Interlead flas shall not exceed 0.017 (0,43) each side.
- 5. Reference JEDEC MS-012 variation AA.



5.2 Recommended PCB Pattern and Stencil Opening



- 1. All linear dimensions are in millimeters.
- 2. This drawing is subject to change without notice.
- 3. Publication IPC-7351 is recommended for alternate designs.
- 4. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- 5. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



12-Feb-2014

PACKAGING INFORMATION

| Orderable Device | Status | Package Type | Package | Pins | Package | Eco Plan | Lead/Ball Finish | MSL Peak Temp | Op Temp (°C) | Device Marking | Samples |
|------------------|---------|--------------|---------|------|---------|----------------------------|------------------|--------------------|--------------|----------------|---------|
| | (1) | | Drawing | | Qty | (2) | (6) | (3) | | (4/5) | |
| CSD88539ND | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | | | Samples |
| CSD88539NDT | PREVIEW | SOIC | D | 8 | 250 | TBD | Call TI | Call TI | | | |

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



| *All dimensions are nominal | |
|-----------------------------|--|
|-----------------------------|--|

| Device | | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|------------|------|--------------------|---|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| CSD88539ND | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|------------|--------------|-----------------|------|------|-------------|------------|-------------|
| CSD88539ND | SOIC | D | 8 | 2500 | 336.6 | 336.6 | 41.3 |

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



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